



100V N-Channel Trench Power MOSFET

General Description

The SJD010N2200 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a wide variety of applications.

Features

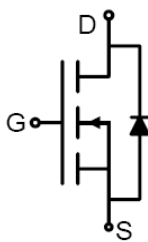
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

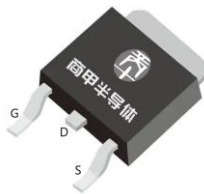
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(ON_TYP)}$	203	mΩ
I_D	5.2	A
Q_G	9	nC



Schematic Diagram



TO-252(DPAK) top view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJD010N2200	SJD010N2200	TO-252	Tape	\	\	2500 Pcs

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	100	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 20	V
I_D	Drain Current-Continuous($T_A=25^{\circ}\text{C}$)	5.2	A
	Drain Current-Continuous($T_A=100^{\circ}\text{C}$)	3.3	A
$I_{DM}(\text{pluse})$	Drain Current-Continuous@ Current-Pulsed (Note 1)	20.8	A
P_D	Maximum Power Dissipation($T_A=25^{\circ}\text{C}$)	13	W
	Maximum Power Dissipation($T_A=100^{\circ}\text{C}$)	5.1	W
E_{AS}	Avalanche energy (Note 2)	9	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		9.8	$^{\circ}\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =100V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1		2.5	V
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =1.5A		3.3		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =1.5A T _J =25℃		203	254	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =1A T _J =25℃		214	285	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V,V _{GS} =0V, f=1.0MHz		381		pF
C _{oss}	Output Capacitance			19		pF
C _{rss}	Reverse Transfer Capacitance			14		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		0.24		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =50V, R _L =33Ω, R _{GEN} =3Ω		2		nS
t _r	Turn-on Rise Time			2		nS
t _{d(off)}	Turn-Off Delay Time			9		nS
t _f	Turn-Off Fall Time			3.6		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =1.5A		9		nC
Q _{gs}	Gate-Source Charge			1.5		nC
Q _{gd}	Gate-Drain Charge			3		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				5.2	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =1.5A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =1.5A, dI/dt=100A/μs		20		ns
Q _{rr}	Reverse Recovery Charge	I _F =1.5A, dI/dt=100A/μs		13		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

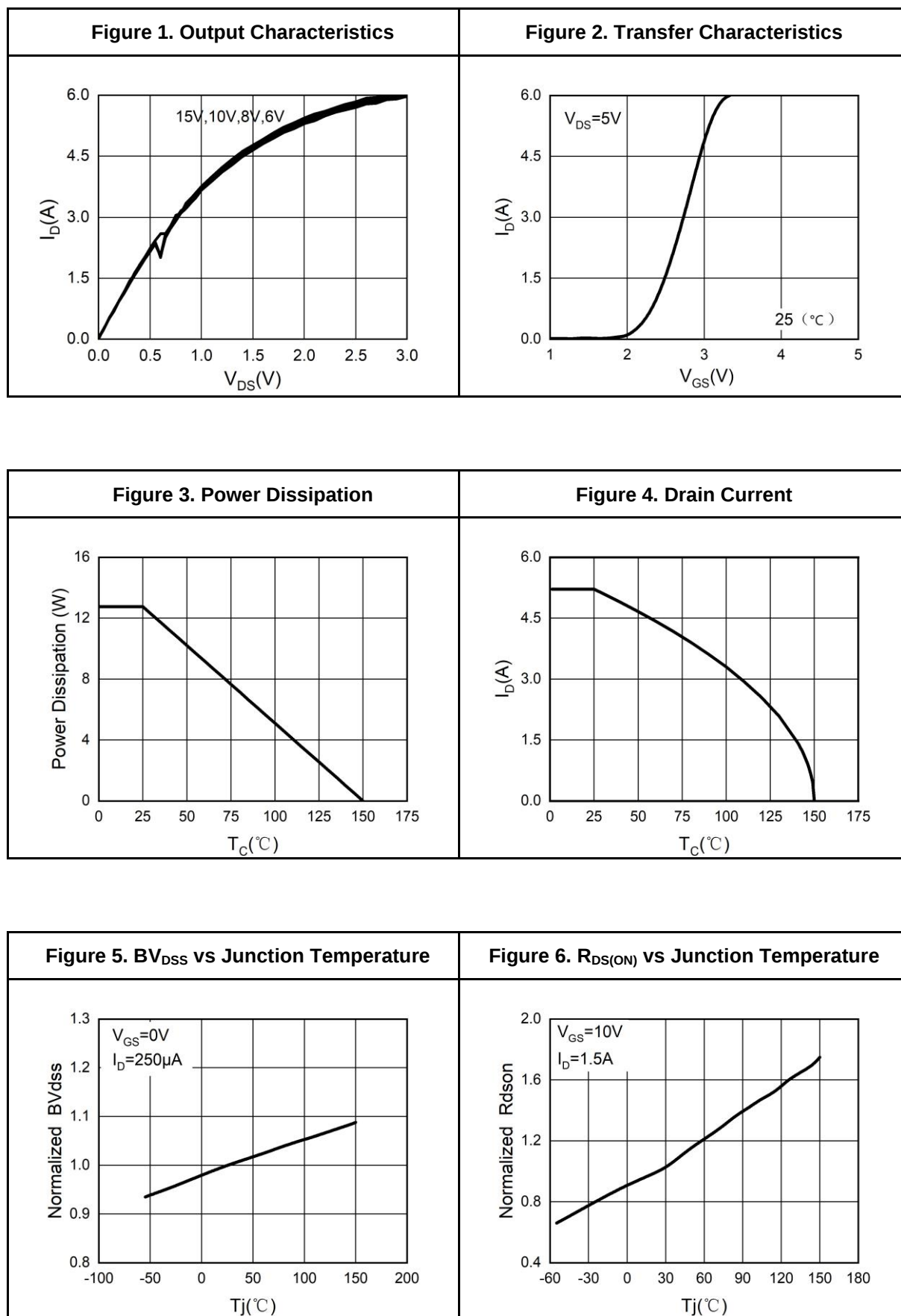
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=60V, V_G=10V, R_g=25\Omega, L=0.5mH$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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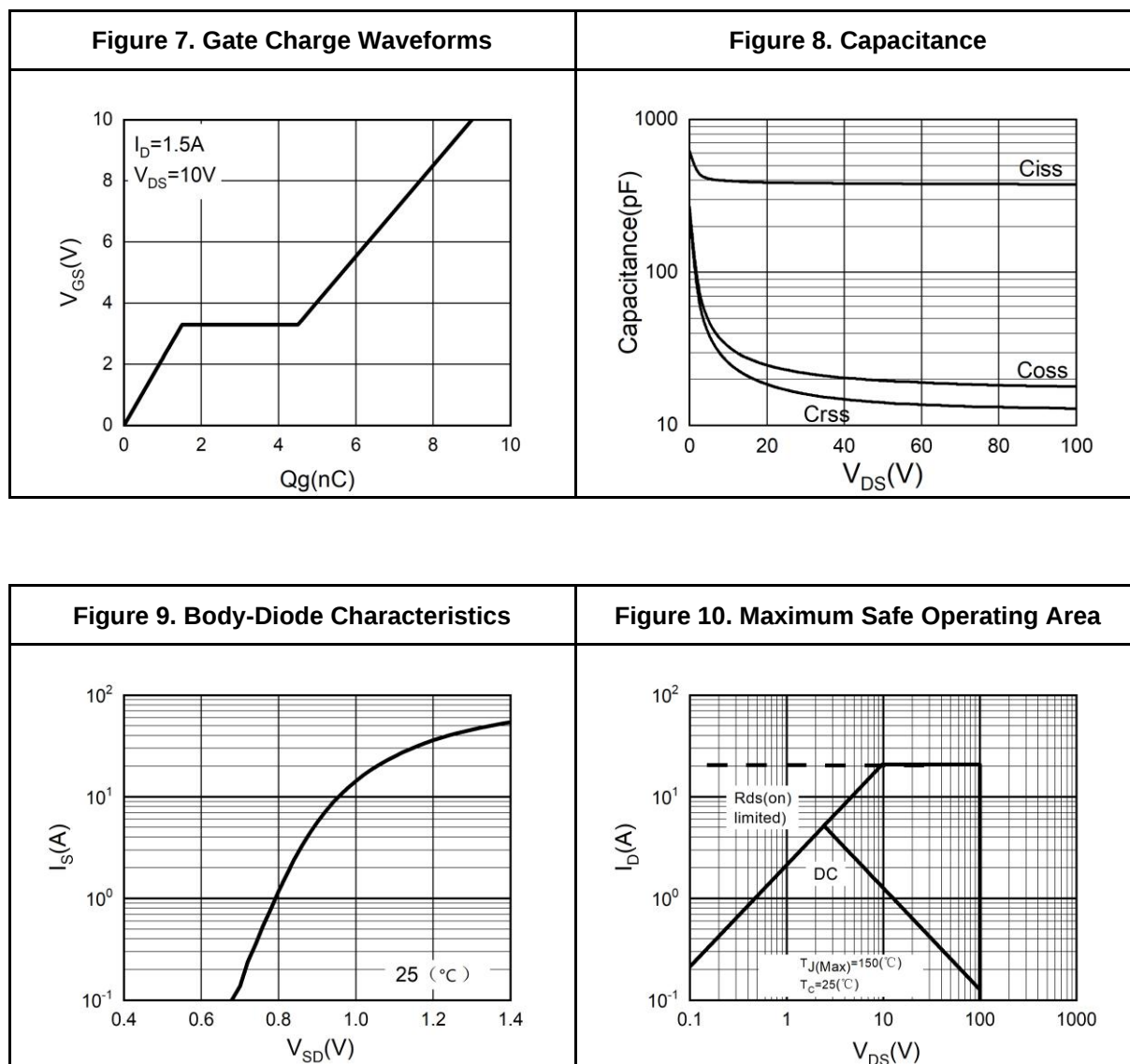
Typical Electrical And Thermal Characteristics (Curves)





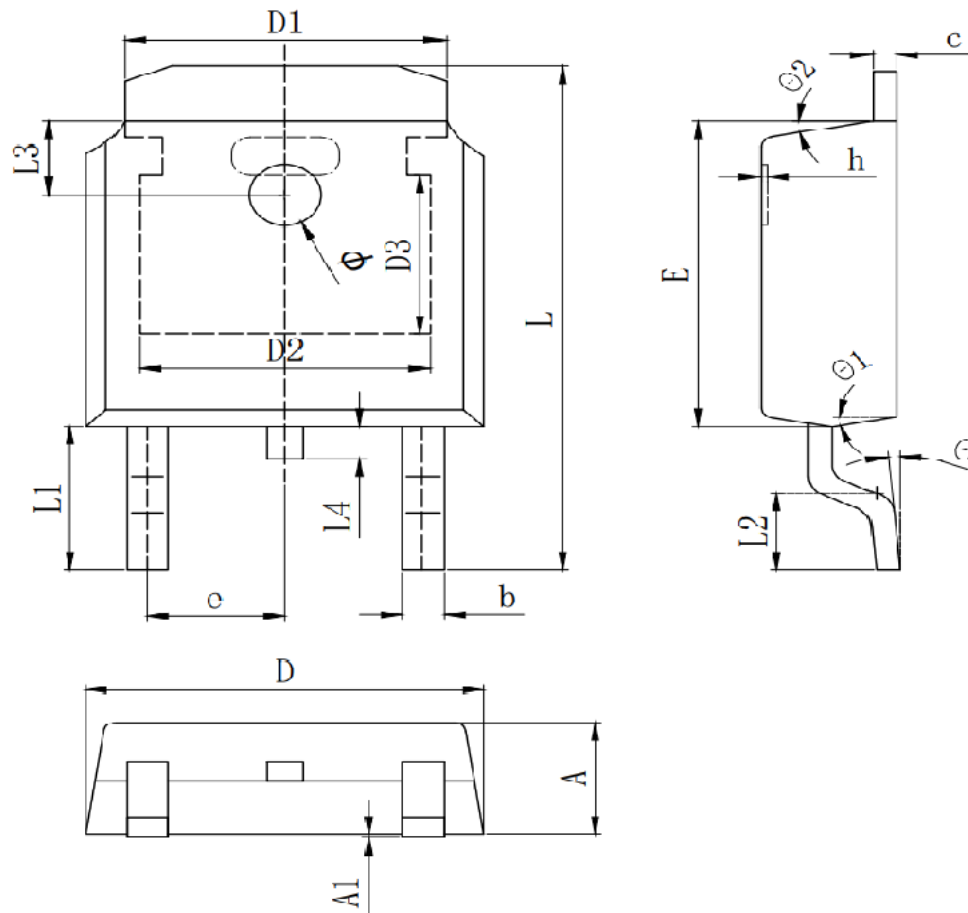
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Typical Electrical And Thermal Characteristics (Curves)





TO-252 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		



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